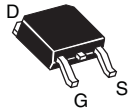


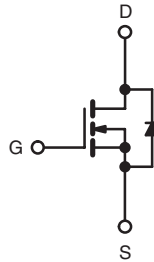
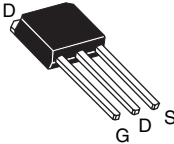
Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	3.0
Q_g (Max.) (nC)	19	
Q_{gs} (nC)	3.3	
Q_{gd} (nC)	13	
Configuration	Single	

DPAK (TO-252)



IPAK (TO-251)



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Surface Mount (IRFR420, SiHFR420)
- Straight Lead (IRFU420, SiHFU420)
- Available in Tape and Reel
- Fast Switching
- Ease of Paralleling
- Compliant to RoHS Directive 2002/95/EC



Available
RoHS*
 COMPLIANT
 HALOGEN
FREE
 Available

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The DPAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU, SiHFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 W are possible in typical surface mount applications.

ORDERING INFORMATION					
Package	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	IPAK (TO-251)
Lead (Pb)-free and Halogen-free	SiHFR420-GE3	SiHFR420TR-GE3 ^a	SiHFR420TRL-GE3 ^a	SiHFR420TRR-GE3 ^a	SiHFU420-GE3
Lead (Pb)-free	IRFR420PbF	IRFR420TRPbF ^a	IRFR420TRLPbF ^a	IRFR420TRRPbF ^a	IRFU420PbF
	SiHFR420-E3	SiHFR420T-E3 ^a	SiHFR420TL-E3 ^a	-	SiHFU420-E3
SnPb	IRFR420	IRFR420TR ^a	IRFR420TRL ^a	IRFR420TRR ^a	IRFU420
	SiHFR420	SiHFR420T ^a	SiHFR420TL ^a	-	SiHFU420

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	500	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25$ °C	2.4	A
		$T_C = 100$ °C	1.5	
Pulsed Drain Current ^a		8.0		
Linear Derating Factor		0.33	W/°C	
Linear Derating Factor (PCB Mount) ^e		0.020		
Single Pulse Avalanche Energy ^b	E_{AS}	400	mJ	
Repetitive Avalanche Current ^a	I_{AR}	2.4	A	
Repetitive Avalanche Energy ^a	E_{AR}	4.2	mJ	
Maximum Power Dissipation	P_D	$T_C = 25$ °C	42	W
Maximum Power Dissipation (PCB Mount) ^e		$T_A = 25$ °C	2.5	
Peak Diode Recovery dV/dt ^c	dV/dt	3.5	V/ns	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature)	for 10 s	260 ^d		

Notes

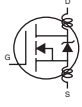
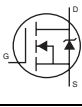
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 124$ mH, $R_g = 25$ Ω , $I_{AS} = 2.4$ A (see fig. 12).
- $I_{SD} \leq 2.4$ A, $dI/dt \leq 50$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	110	°C/W
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	50	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.0	

Note

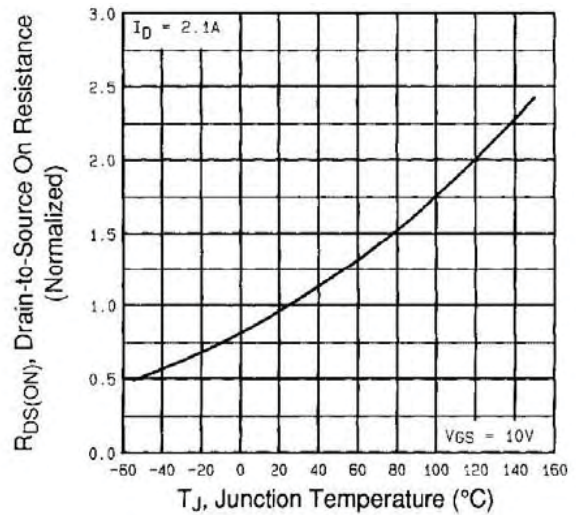
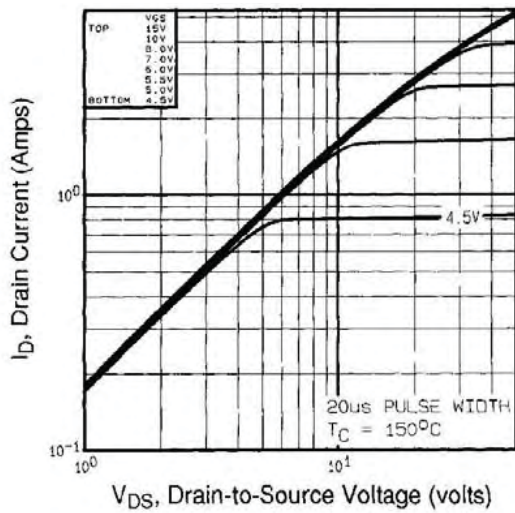
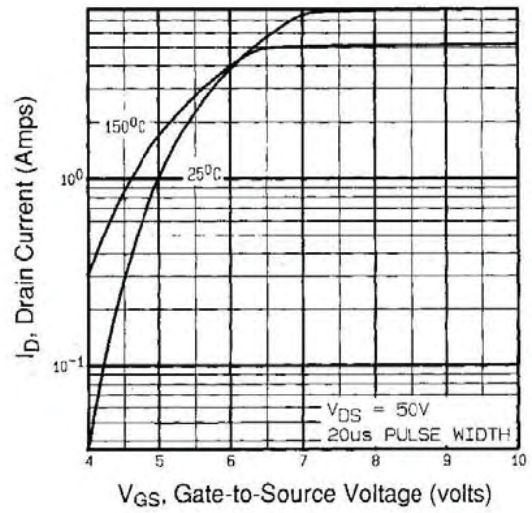
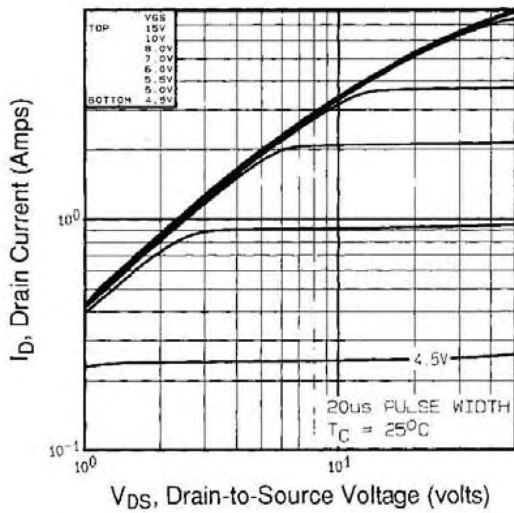
a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX. UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	- V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.59	- V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0 V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100\text{ nA}$	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	25 μA	
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250 μA	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 1.4\text{ A}^b$	-	-	3.0 Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 1.4\text{ A}$		1.5	-	- S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	360	-	
Output Capacitance	C_{oss}			-	92	-	pF
Reverse Transfer Capacitance	C_{rss}			-	37	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 2.1\text{ A}, V_{DS} = 400\text{ V}$, see fig. 6 and 13 ^b	-	-	19	
Gate-Source Charge	Q_{gs}			-	-	3.3	nC
Gate-Drain Charge	Q_{gd}			-	-	13	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 2.1\text{ A}, R_g = 18\text{ }\Omega, R_D = 120\text{ }\Omega$, see fig. 10 ^b		-	8.0	-	
Rise Time	t_r			-	8.6	-	ns
Turn-Off Delay Time	$t_{d(off)}$			-	33	-	
Fall Time	t_f			-	16	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	
Internal Source Inductance	L_S			-	7.5	-	nH
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	2.4	
Pulsed Diode Forward Current ^a	I_{SM}			-	-	8.0	A
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 2.4\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.6 V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 2.1\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	260	520 ns	
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.70	1.4 μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



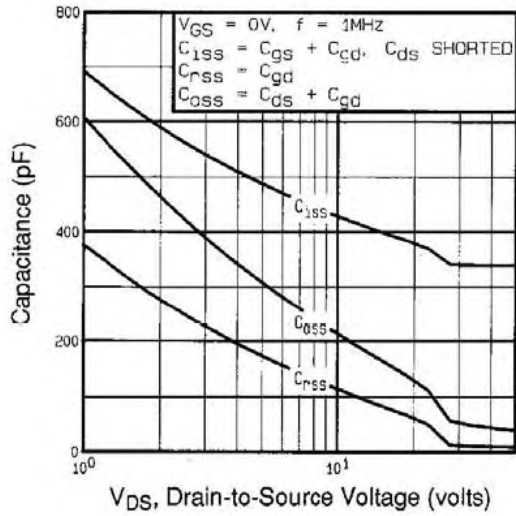


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

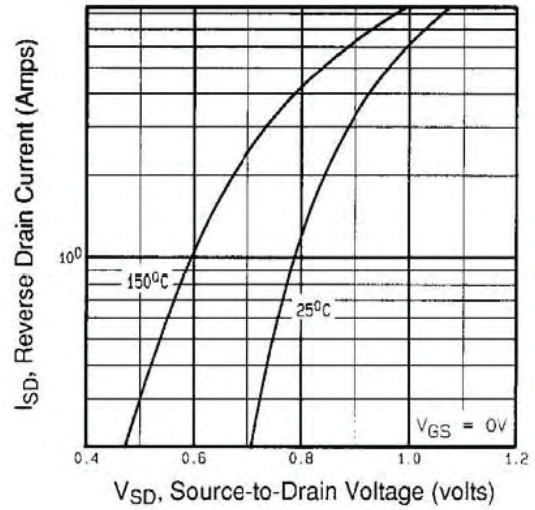


Fig. 7 - Typical Source-Drain Diode Forward Voltage

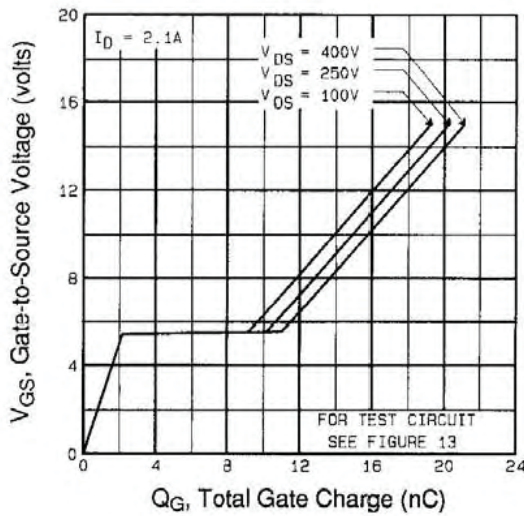


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

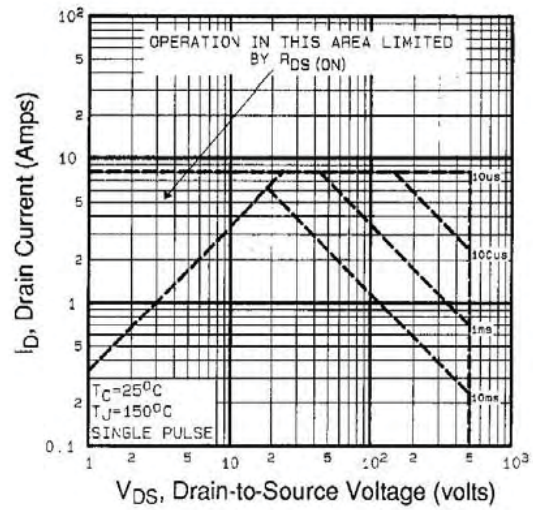


Fig. 8 - Maximum Safe Operating Area

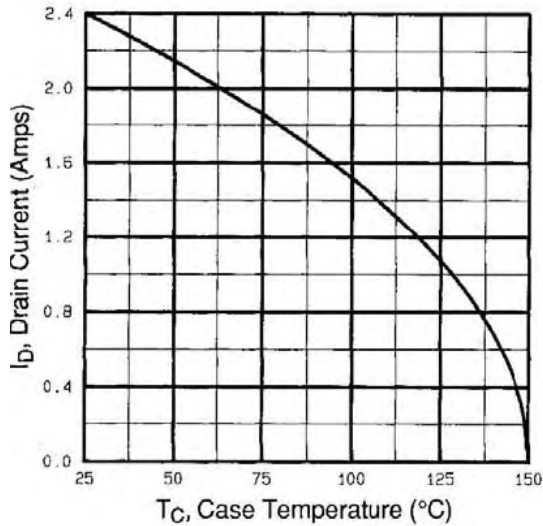


Fig. 9 - Maximum Drain Current vs. Case Temperature

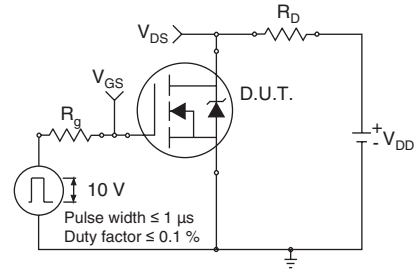


Fig. 10a - Switching Time Test Circuit

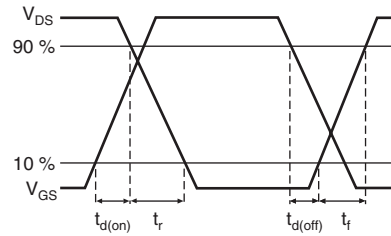


Fig. 10b - Switching Time Waveforms

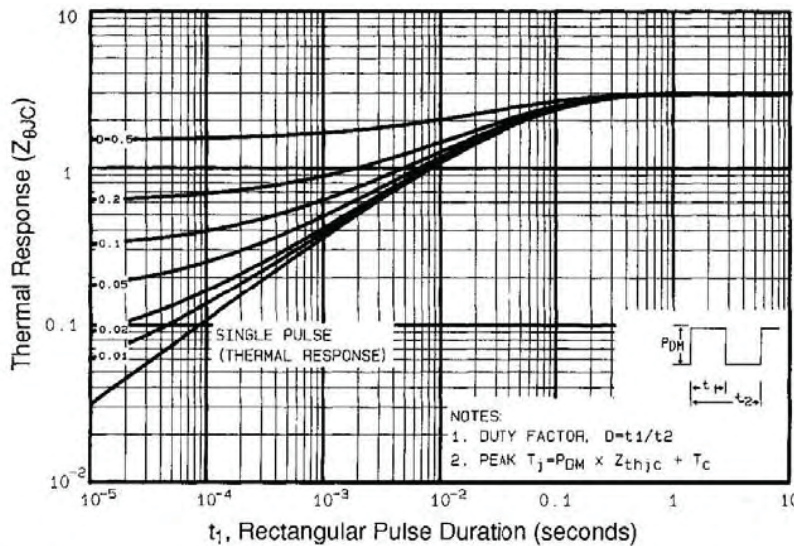


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

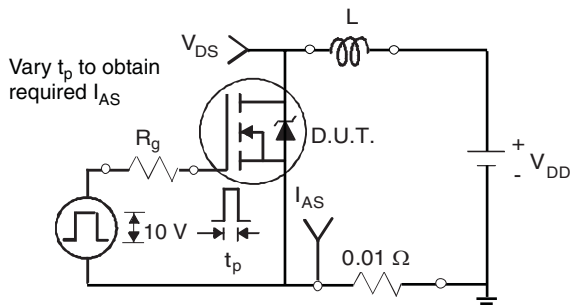


Fig. 12a - Unclamped Inductive Test Circuit

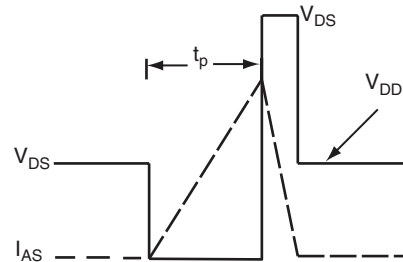


Fig. 12b - Unclamped Inductive Waveforms

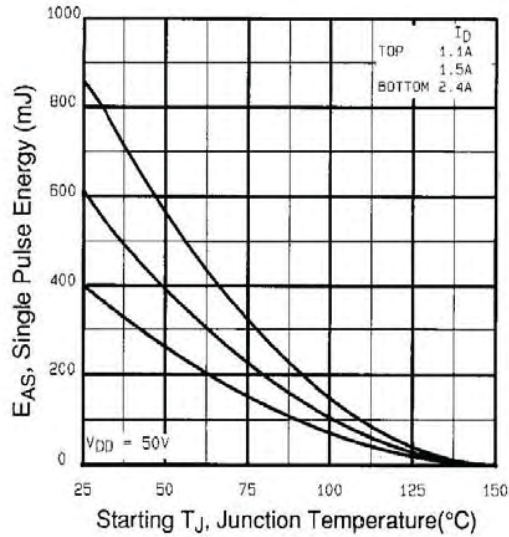


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

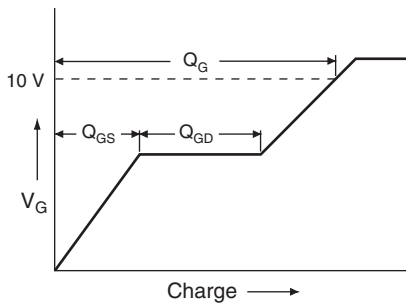


Fig. 13a - Basic Gate Charge Waveform

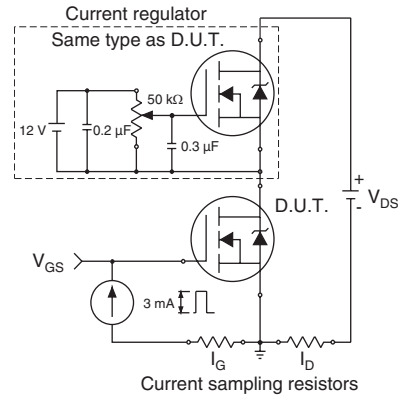
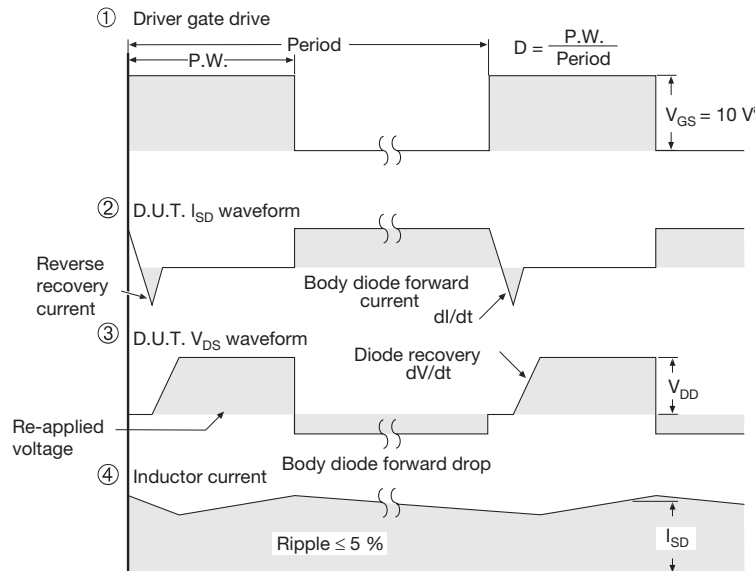
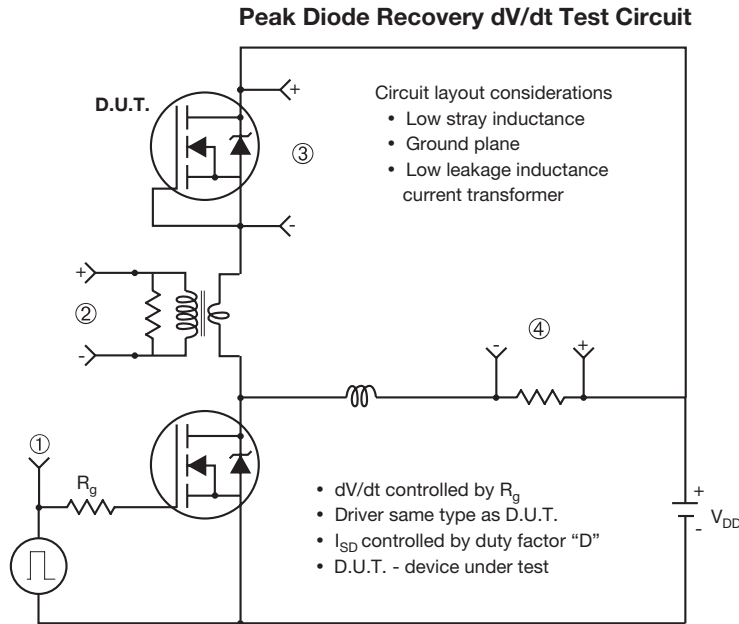


Fig. 13b - Gate Charge Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 -For N-Channel

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